

SKKT 162 H4, SKKH 162 H4



SEMIPACK[®] 2

Thyristor / Diode Modules

SKKH 162 H4

SKKT 162 H4

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

Typical Applications*

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 250$ A (maximum value for continuous operation) $I_{TAV} = 162$ A (sin.180; $T_c = 77$ °C)	
2100	2000	SKKT 162/20E H4	SKKH 162/20E H4
2300	2200	SKKT 162/22E H4	SKKH 162/22E H4

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	143 (101)	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 125$ °C; 10 ms	5200 4800	A A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 125$ °C; 8,3 ... 10 ms	135000 115000	A ² s A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 500$ A	max. 1,65	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 0,95	V
r_T	$T_{vj} = 125$ °C	max. 2	mΩ
$I_{DD}; I_{RD}$	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 60	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 200	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/μs
t_q	$T_{vj} = 125$ °C	50 ... 150	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 400	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 1000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 2	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,16 / 0,08	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,17 / 0,085	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,19 / 0,095	K/W
$R_{th(c-s)}$	per thyristor / per module	0,1 / 0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminal	5 ± 15 %	Nm
a		5 * 9,81	m/s ²
m	approx.	175	g
Case	SKKT SKKH	A 21 A 22	



SKKT

SKKH

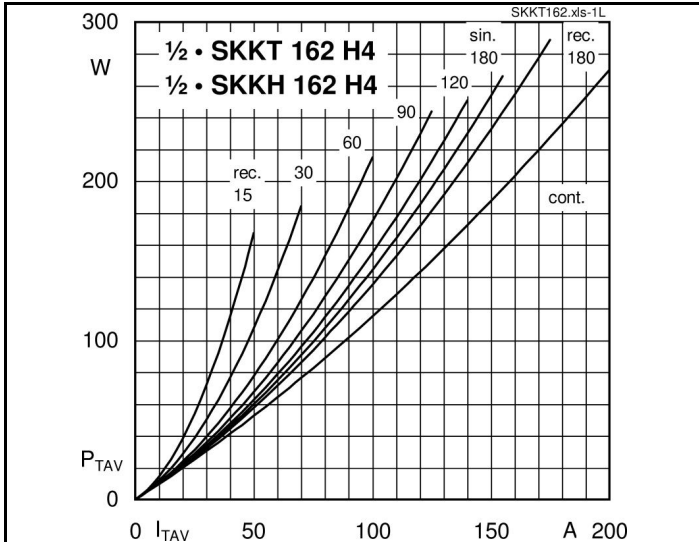


Fig. 1L Power dissipation per thyristor vs. on-state current

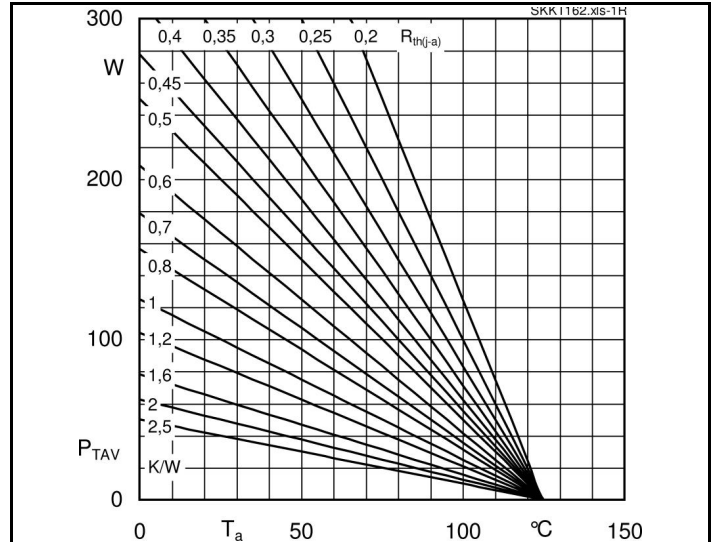


Fig. 1R Power dissipation per thyristor vs. ambient temp.

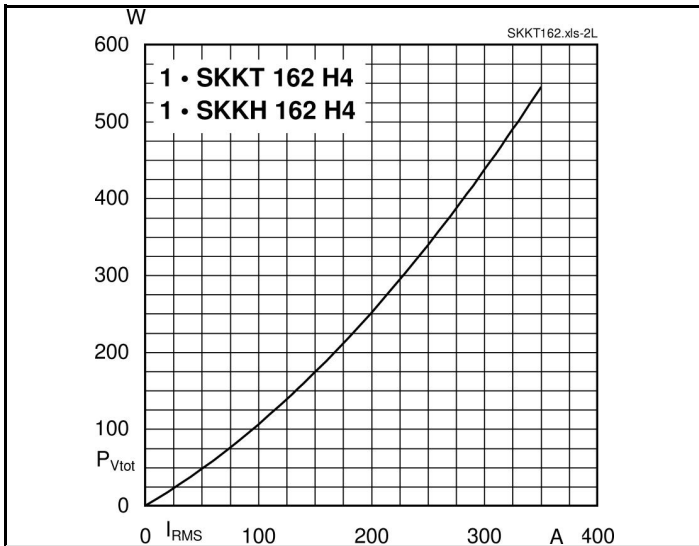


Fig. 2L Power dissipation per module vs. rms current

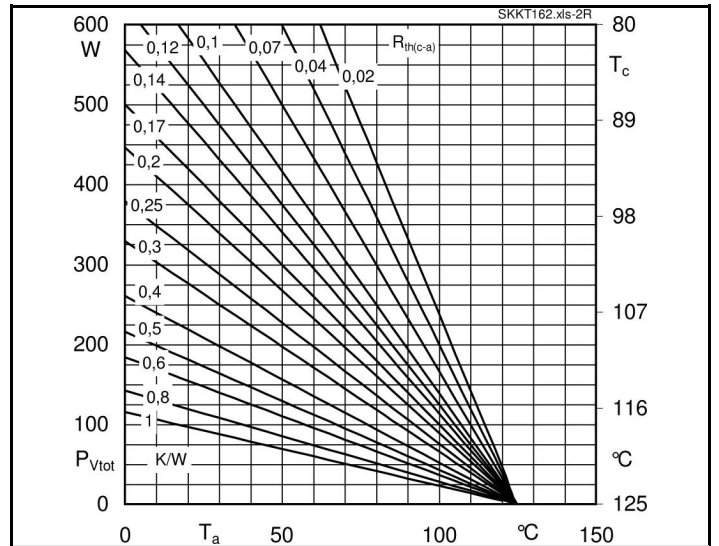


Fig. 2R Power dissipation per module vs. case temp.

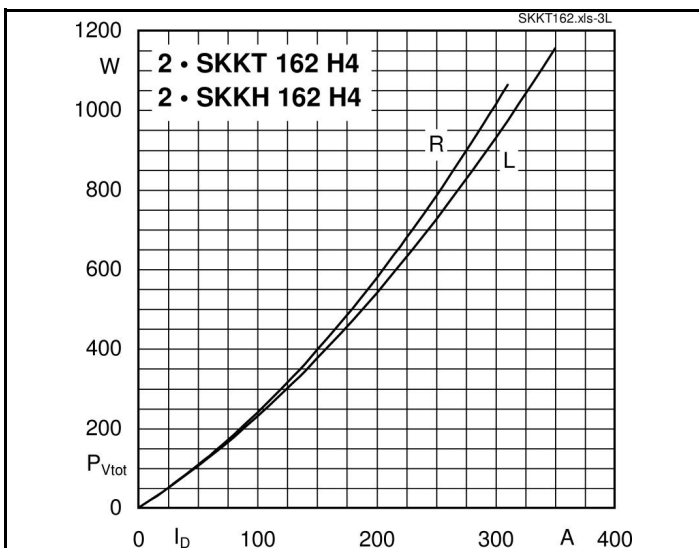


Fig. 3L Power dissipation of two modules vs. direct current

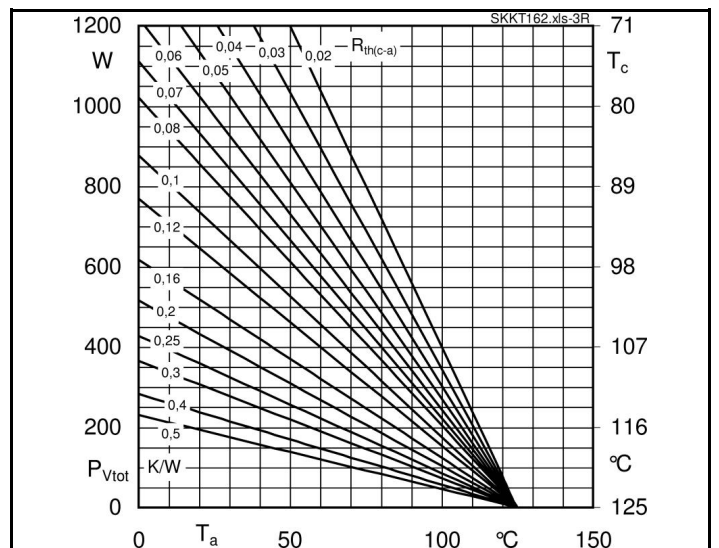
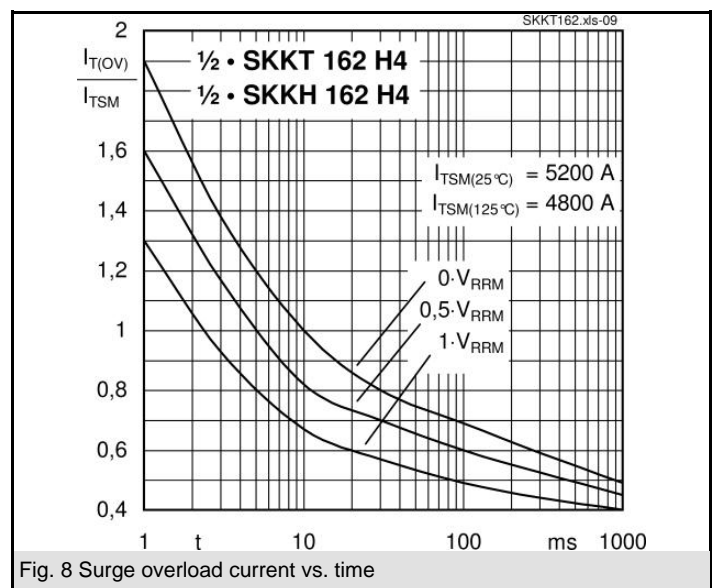
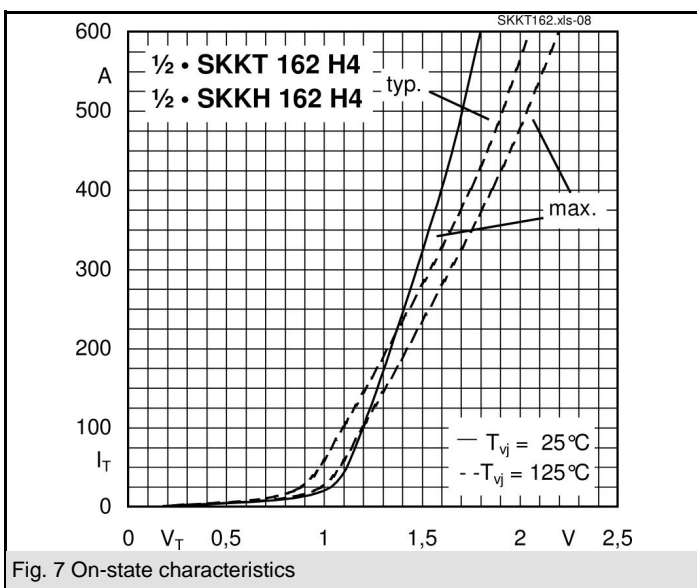
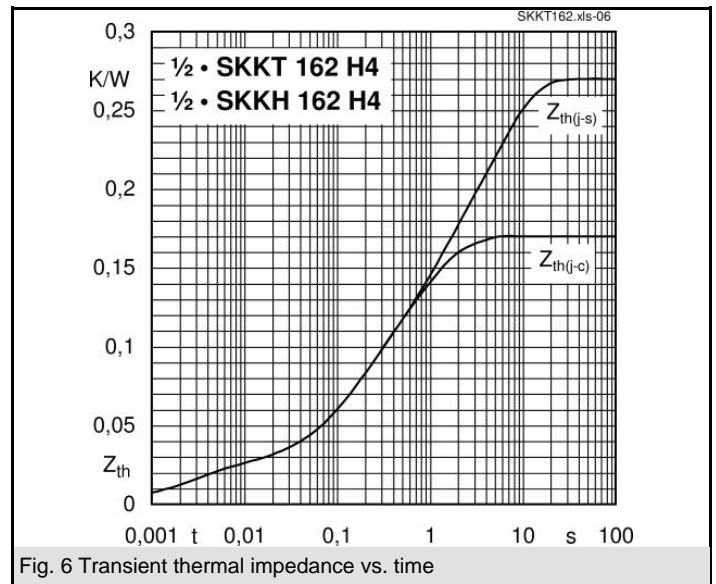
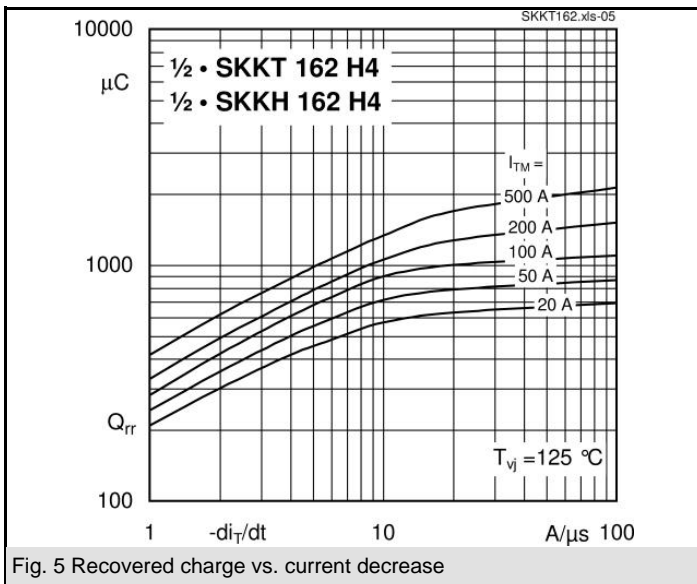
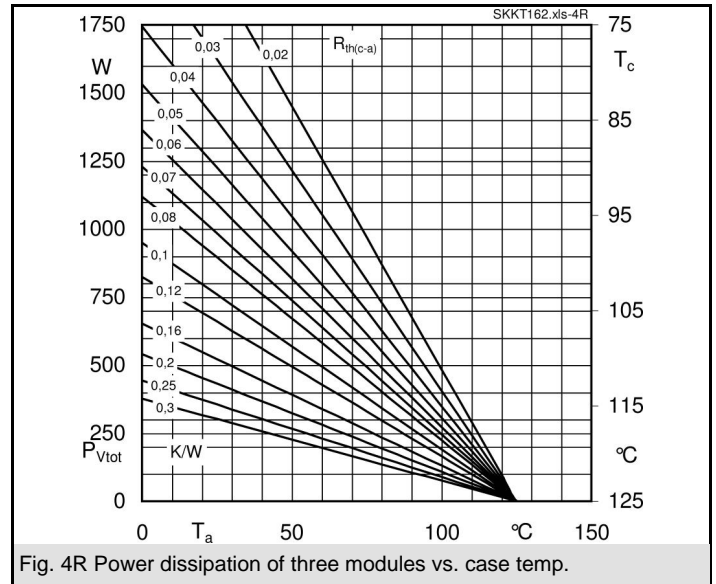
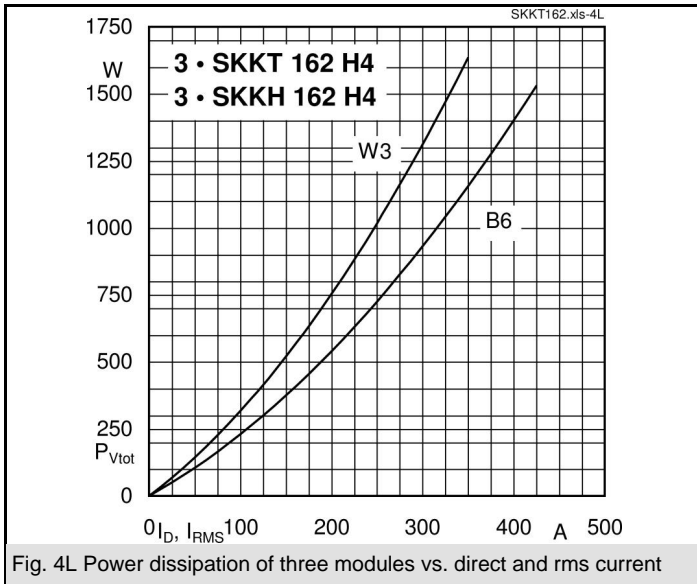


Fig. 3R Power dissipation of two modules vs. case temp.

SKKT 162 H4, SKKH 162 H4



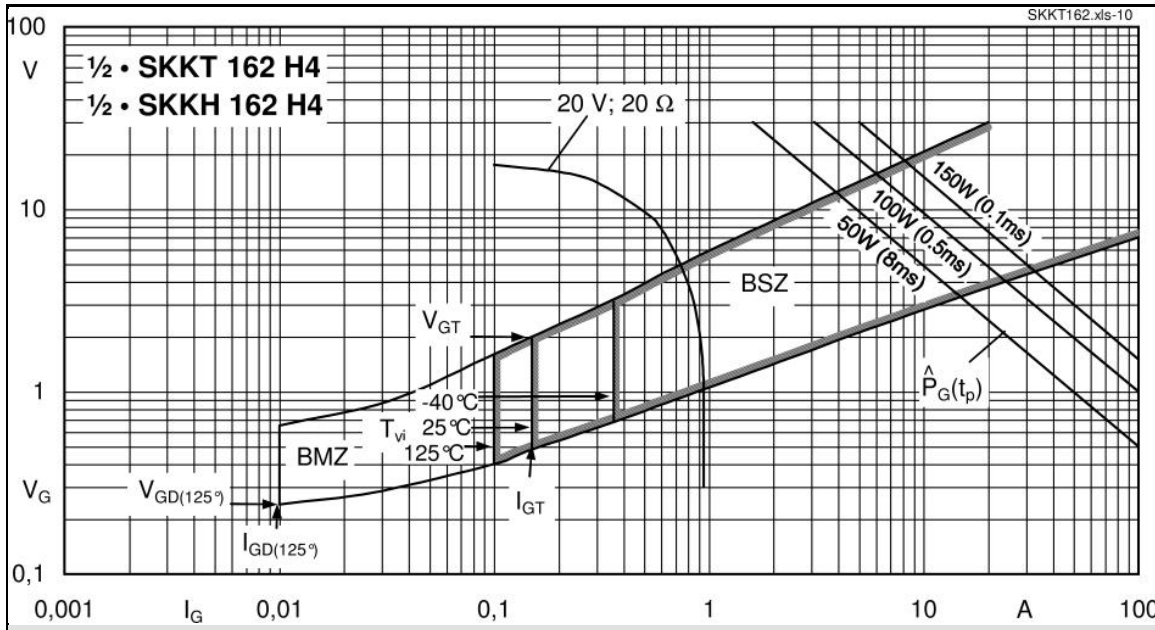
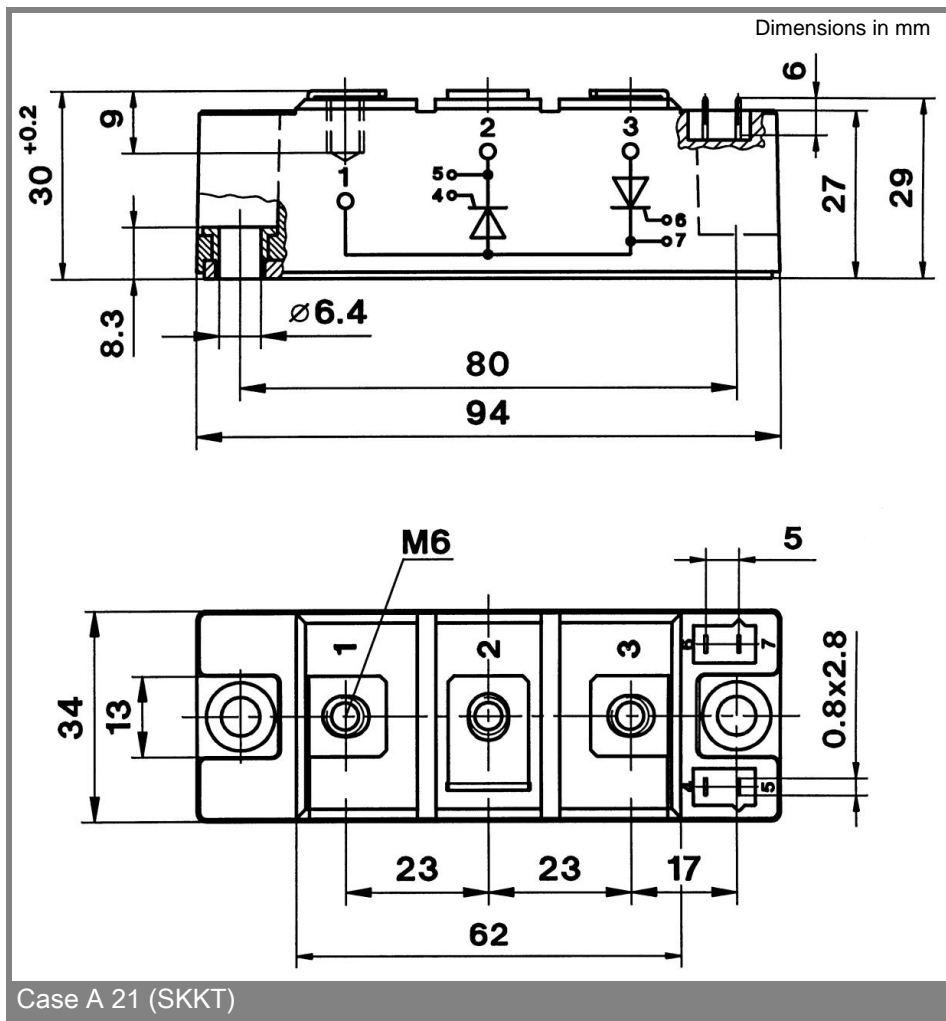


Fig. 9 Gate trigger characteristics



* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON

SKKT 162 H4, SKKH 162 H4

products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.